

Notice of References CitedApplication No.
08/691,434Applicant(s)
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1107

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*		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
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	B	4,475,027	10/1984	Pressley	----	----
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* A copy of this reference is not being furnished with this Office action.
(See Manual of Patent Examining Procedure, Section 707.05(a).)